

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s):

K. OHNISHI et al

Serial No.:

09/829,969

Filed:

April 11, 2001

For:

STACKED GATE ELECTRODE FOR A MOS TRANSISTOR

OF A SEMICONDUCTOR DEVICE (As Amended)

Group:

2818

Examiner:

MAI H.C. TRAN

AMENDMENT

Assistant Commissioner of Patents Washington, D. C. 20231

Sept. 3, 2002

Sir:

In response to the Office Action dated April 1, 20092, the period of response for which extension of time is requested in the attached Petition for Extension of Time, the following amendments and remarks are respectfully

submitted in connection with the above-identified application.

01 FC:102 02 FC:103

84.00 OP 108.00 OP

IN THE TITLE:

Please amend the title to read as follows:

K

STACKED GATE ELECTRODE FOR A MOS TRANSISTOR OF A SEMICONDUCTOR DEVICE

IN THE SPECIFICATION:

Please **replace** the originally submitted Specification with the Substitute Specification enclosed herewith as Attachment A.